1 2	Number			DB	m:
4	:	((""densified dielectric"").PN.		Time stamp
			/ · Lin.	USPAT;	2002/07/18 16:1
- [1		US-PGPUB;	
7	'		(""densified"").PN.	EPO; JPO	
			(demotited).FN.	USPAT;	2002/07/18 17:1
-		ŀ		US-PGPUB;	
1	2		/ / / / / / / / / / / / / / / / / / /	EPO; JPO	
- 1	3	1	I COMBILIED I.FN.	USPAT	2002/07/18 17:1
1		8939		USPAT	2002/07/18 17:1
1		71	delectric	USPAT	2002/07/18 17:1
1		616	densification same dielectric	TIODEM	2002/07/18 17:1
1		25	(densification near dielectric) and plasma	USPAT	2002/07/18 17:1
1	7	697	"low k dielectric"		2002/07/18 17:2
1				USPAT;	2002/07/18 17:23
				US-PGPUB;	
2	2	105	"Torr le alt -1	EPO; JPO	
-	_	103	"low k dielectric" same "etch stop"	USPAT;	2002/07/18 17:38
	[US-PGPUB;	2002/07/10 17:38
1	,			EPO; JPO	1
2	I	1			1
28	3	271	treat\$3 near dielectric	USPAT	2002/07/18 17:48
l			4201000110	USPAT;	2002/07/18 17:49
	1			US-PGPUB;	
33	3	87	(treats) non diele .	EPO; JPO	
	ſ	0 /	(treat\$3 near dielectric) and plasma	USPAT;	2002/07/18 17:53
				US-PGPUB;	2002/01/18 17.53
38	, [EPO; JPO	
50	'	11		USPAT;	2000/07/10
	1		"etch stop"		2002/07/18 17:56
	1		-	US-PGPUB;	
43	İ	2	5314845.pn.	EPO; JPO	İ
				USPAT;	2002/07/18 17:58
				US-PGPUB;	1
48	ĺ	2	F01 F000	EPO; JPO	İ
	ľ	2	5915203.pn.	USPAT;	2002/07/18 18:00
	1			US-PGPUB;	2002/07/18 18:00
53	1	_		EPO; JPO	
		2	("6303047" "6365528").pn.	USPAT;	00001
			,		2002/07/18 18:06
		j		US-PGPUB;	1
58	ļ	44591	silicon with carbide	EPO; JPO	1
		j	with calbide	USPAT;	2002/07/18 18:06
		j		US-PGPUB;	1
63	[42528	oiline tu	EPO; JPO	
••	j	42320	silicon with carbon	USPAT;	2002/07/10 10 07
	[ĺ		US-PGPUB;	2002/07/18 18:07
	ſ	1		US-FGPUB;	
68	I	73891	(silicon with carbide) or (silicon with	EPO; JPO	
		İ	carbon)	USPAT;	2002/07/18 18:07
	1	1		US-PGPUB;	
73	1	19286	(/silicon with and)	EPO; JPO	
			((silicon with carbide) or (silicon with	USPAT;	2002/07/18 18:09
	ĺ		carbon)) same (plasma densified plasma	US-PGPUB;	2002/07/10 10:09
		J	mydlogen ne Hellum Ar Argon NH3 ammonia NG	EPO; JPO	
78	ĺ	1	niclogen)	110, 010	
0	ĺ	189	(((silicon with carbide) or (silicon with	HODAM	
	1	ļ		USPAT;	2002/07/18 18:10
	1	1.		US-PGPUB;	
	[1:	nitrogen)) and "low k"	EPO; JPO	ŀ
33	1	167			ŀ
	ĺ	10,	((((silicon with carbide) or (silicon with	USPAT;	2002/07/18 18:10
	1	, ,	carbon) Same (plasma densified plasma	US-PGPUB;	2002/0//18 18:10
	1	, ,	mydlogen ne hellum Ar Argon NH3 ammonia Na	EPO; JPO	
	1	1	nitrogen)) and "low k") and etch\$3	Pro, 050	